

L Number	Hits	Search Text	DB	Time stamp
-	997	257/57	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 11:48
-	1675	257/59	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:24
-	1323	257/72	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:10
-	80	438/609	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:10
-	682	438/149	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:11
-	96	438/341	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:11
-	173	437/181	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:11
-	349	438/48	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:11
-	1641	438/128	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:12
-	863	438/151	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:13
-	207	438/157	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:13
-	636	438/166	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:13
-	889	257/59 and transparent and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 09:19
-	1	257/581 and transparent and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:38

-	67	257/59 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:55
-	45	257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 17:49
-	13	257/57 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 15:12
-	1	257/359 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:55
-	5	437/181 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
-	1	438/609 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
-	8	438/149 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
-	1	438/48 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 17:56
-	1	438/128 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 07:40
-	11	438/151 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:21
-	3	438/157 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:09
-	4	438/166 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/17 18:22
-	289	el and transparent and (thin adj film and transistor) and (257/\$.ccls. or 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:01
-	1	"6235561".PN.	USPAT	2002/04/18 11:45
-	1	"5446562".PN.	USPAT	2002/04/18 15:01

-	262	257/57 and ((silicon adj oxide) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 18:36
-	6	257/57 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:57
-	12	257/59 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 16:02
-	10	257/72 and ((protective adj insulating adj film) same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:16
-	2	257/57 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:11
-	6	257/59 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:59
-	3	257/72 and ((protective adj insulating adj film) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:59
-	7	TFT and ((protective adj insulating adj film) same (amorphous adj silicon)) and (257/\$.ccls. or 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 12:58
-	6	TFT and ((protective adj insulating adj film) WITH (amorphous adj silicon)) and (257/\$.ccls. or 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 12:59
-	6	257/72 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
-	10	257/59 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
-	8	257/57 and ((protective adj insulating adj film) same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 13:17
-	38	257/72 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:12
-	37	257/59 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 15:12

-	24	257/57 and ((silicon adj oxide) same defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:19
-	837	257/72 and transparent and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:17
-	51	257/72 and transparent and (thin adj film adj transistor) and (thickness near (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:37
-	1	257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) near2 ("100" nm))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:40
-	11	257/72 and transparent and (thin adj film adj transistor) and ((protective adj insulating adj film) with ("100" nm))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 17:45
-	1	"6046479".PN.	USPAT	2002/10/23 13:32
-	5	257/59 and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:50
-	2	257/72 and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 15:49
-	6	257/\$.ccls. and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:47
-	2	438/\$.ccls. and ((protective adj insulating adj film) with defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 16:06
-	17	(protective adj insulating adj film) with defect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 16:10
-	6	257/72 and transparent and (thin adj film adj transistor) and (liquid adj crystal) and (alignment adj layer) and (counter adj substrate) and (counter adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 18:34
-	566	(organic adj 'EL') and (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:02
-	114	(organic adj 'EL') and (thin adj film adj transistor) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:06
-	7	(organic adj 'EL') and (cathode adj layer) and (anode adj layer) and (thin adj film adj transistor) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/23 19:07

-	7	257/\$.ccls. and ((amorphous adj film) with oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:58
-	7	257/\$.ccls. and (oxidation with (amorphous adj film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 17:10
-	1	(surface adj oxidation) near2 (amorphous adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 17:44
-	20	(thermal adj oxidation) SAME (amorphous adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 16:35
-	102	(surface near2 (amorphous adj silicon)) with oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 10:09
-	74	(surface near2 (amorphous adj silicon)) near5 oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 10:44
-	3	nitride with ((surface near2 (amorphous adj silicon)) near5 oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 10:59
-	1	nitride near5 ((surface near2 (amorphous adj silicon)) near5 oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 10:59
-	19	surface with (amorphous adj film) with oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 08:33
-	245	438/150	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 08:38
-	193	438/150 and (TFT or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 10:24
-	787	438/151 and (TFT or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 10:26
-	108	438/151 and (TFT or (thin adj film adj transistor)) and (surface with (amorphous adj silicon) with (oxide or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 10:30
-	233	438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 10:32

-	113	438/151 and (TFT or (thin adj film adj transistor)) and ((amorphous adj silicon) with (oxide or oxidation)) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/11 10:33
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